

PJW4N06A

60V N-Channel Enhancement Mode MOSFET

Voltage	60 V	Current	4.0 A
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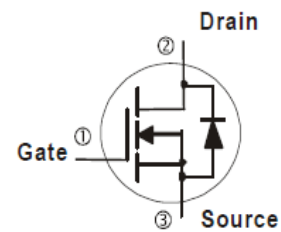
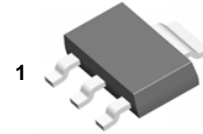
Features

- $R_{DS(ON)}, V_{GS}@10V, I_D@3.0A < 100m\Omega$
- $R_{DS(ON)}, V_{GS}@4.5V, I_D@2.0A < 110m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W4N06A

SOT-223



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _A =25°C	I _D	4	A
	T _A =70°C		3.2	
Pulsed Drain Current (Note 1)		I _{DM}	8	A
Power Dissipation	T _A =25°C	P _D	3.1	W
	T _A =70°C		2	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 5)		R _{θJA}	40.3	°C/W

- Limited only By Maximum Junction Temperature

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0	1.86	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3.0A	-	85	100	mΩ
		V _{GS} =4.5V, I _D =2.0A	-	95	110	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q _g	V _{DS} =48V, I _D =3A, V _{GS} =4.5V (Note 2,3)	-	5.1	-	nC
Gate-Source Charge	Q _{gs}		-	1.2	-	
Gate-Drain Charge	Q _{gd}		-	1.9	-	
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	509	-	pF
Output Capacitance	C _{oss}		-	39	-	
Reverse Transfer Capacitance	C _{rss}		-	26	-	
Turn-On Delay Time	td(on)	V _{DD} =30V, I _D =3A, V _{GS} =10V, R _G =3.3Ω (Note 2,3)	-	1.6	-	ns
Turn-On Rise Time	tr		-	7.3	-	
Turn-Off Delay Time	td(off)		-	25	-	
Turn-Off Fall Time	tf		-	14	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	4	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.8	1.2	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature T_J(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J = 25°C.
4. The maximum current rating is package limited
5. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing

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TYPICAL CHARACTERISTIC CURVES

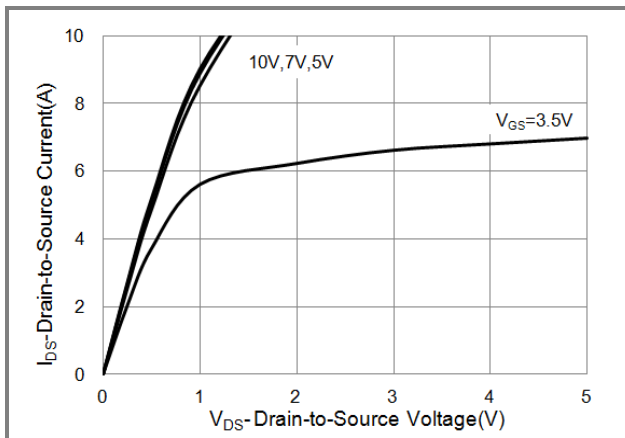


Fig.1 Output Characteristics

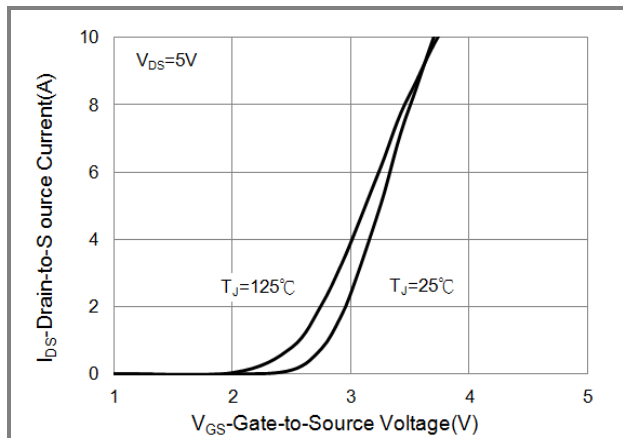


Fig.2 Transfer Characteristics

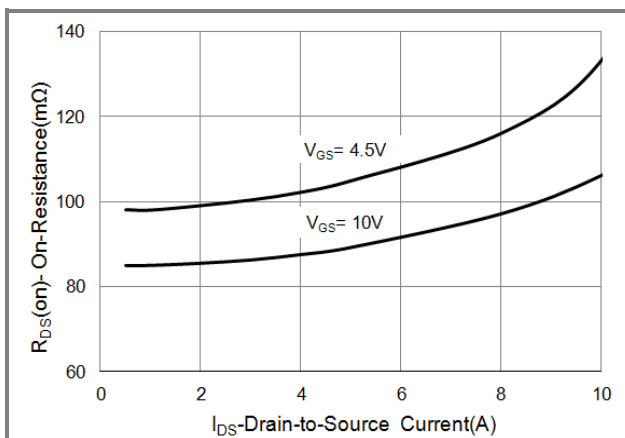


Fig.3 On-Resistance vs. Drain Current

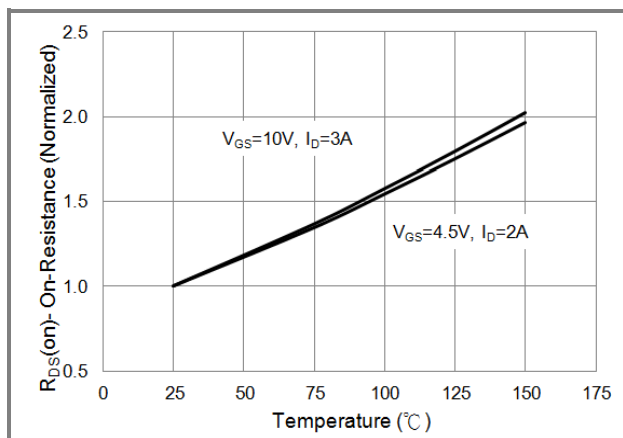


Fig.4 On-Resistance vs. Junction temperature

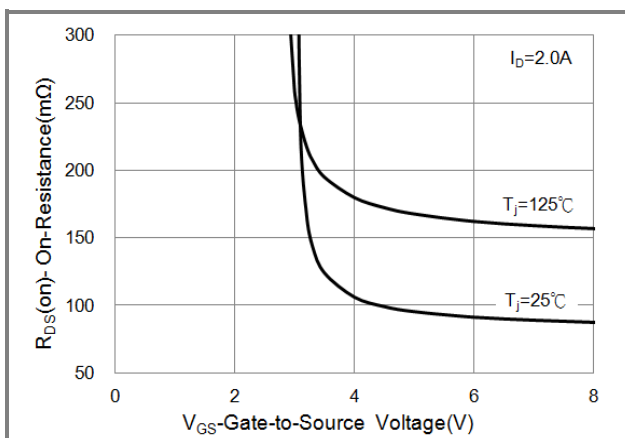


Fig.5 On-Resistance Variation with V_{GS} .

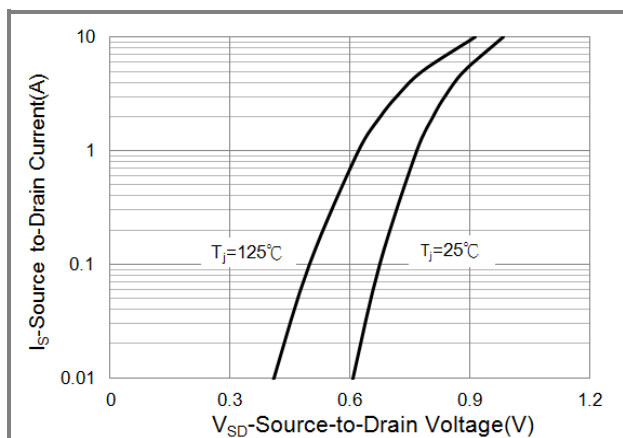


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

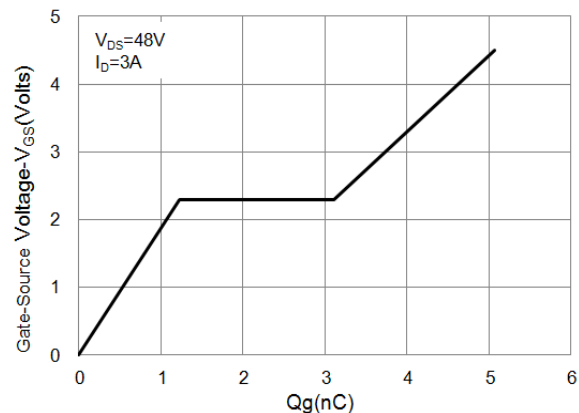


Fig.7 Gate-Charge Characteristics

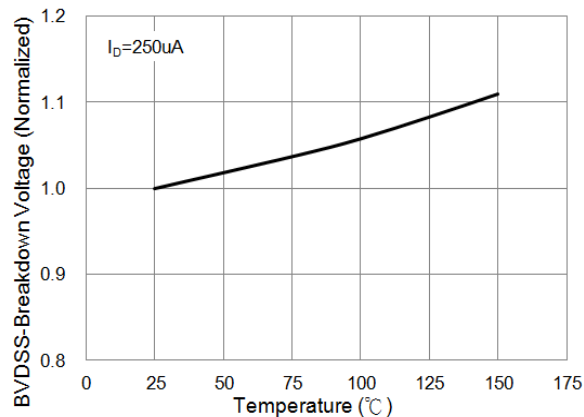


Fig.8 Breakdown Voltage Variation vs. Temperature

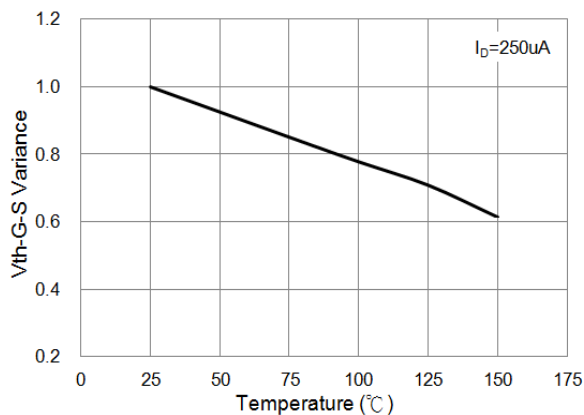


Fig.9 Threshold Voltage Variation with Temperature

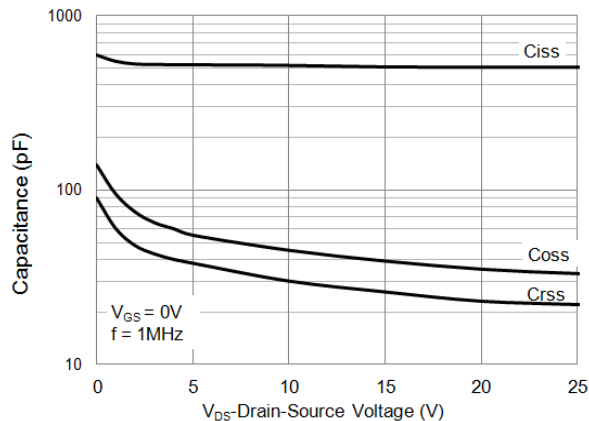


Fig.10 Capacitance vs. Drain-Source Voltage

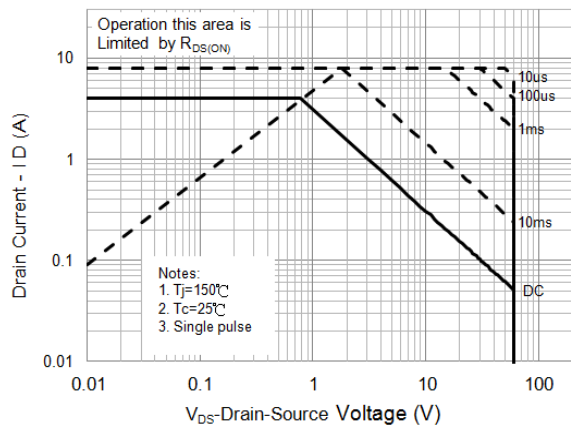
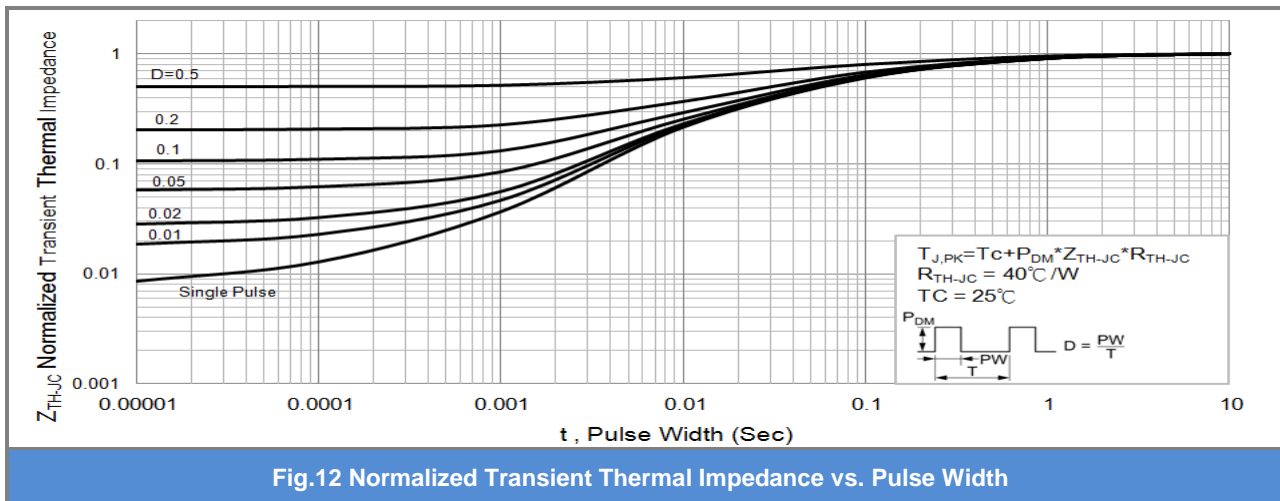


Fig.11 Maximum Safe Operating Area

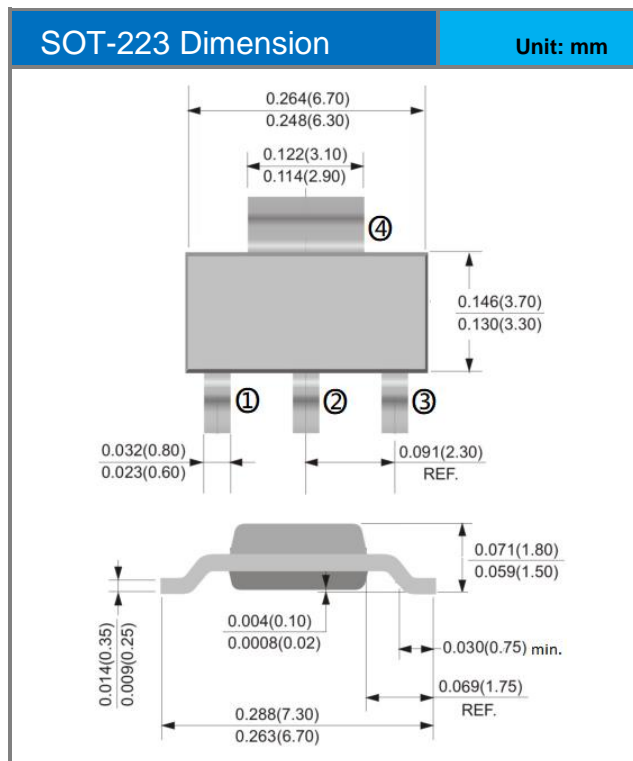
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TYPICAL CHARACTERISTIC CURVES



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Packaging Information

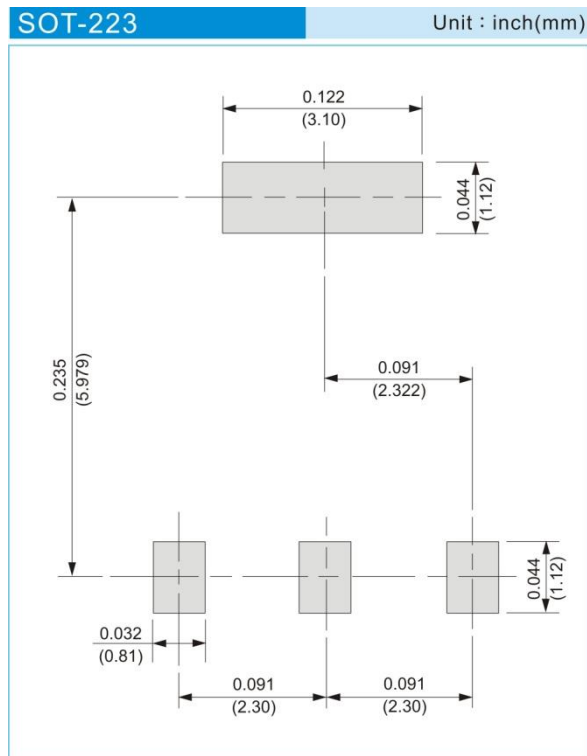


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Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJW4N06A	SOT-223	2,500pcs / 13" reel	W4N06A

Mounting Pad Layout



PJW4N06A

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